

Abstract

The invention allows to create a transistor which can operates on supply pressure 120 volt and over (to some kilovolt), that is the transistor can be both closed and open with any polarity of a voltage on drain-source. It simplifies designing of many circuits and provides creating of circuits which cannot be produced with any other types of transistors. Besides, the transistor has high technical characteristics: a high current dencity, a high switching power, a very low on-voltage. It provides applying of the transistor for production, transfer and use of an electric energy. This is achieved with disposing elements of a bipolar static induction transistor: a gate, a source, a channel and electrodes -- on each of sides of a lightly doped substrate, besides one of channels of multielement structure is thicker than other channels, said channel is connected to a separate electrode.

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